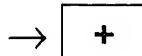


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	
				Filing Date	
				First Named Inventor <i>Lampert et al.</i>	
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number <i>AFD 504</i>	

J1017 U.S. PTO
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.*	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER DOCUMENTS (Including Author, Title, Date, Pages, etc.)			
MS			Fissel et al. "Low-temperature growth of SiC thin films on Si and 6H-SiC by solid-source molecular beam epitaxy" Applied Physics Letters, Vol. 66 No. 23, pp. 3182-31844, June 5, 1995, American Institute of Physics
Examiner Signature		<i>Matthew Song</i>	Date Considered <i>1/9/2002</i>